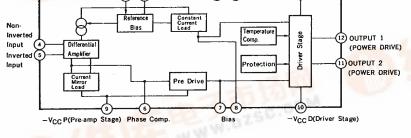
N E C ELECTRONICS TNC DEE DE 查询UPC134<u>2V供应商</u> ₩42724世期通過第164 6427525 N E C ELECTRONICS INC 00000 05E 23064 D **BIPOLAR ANALOG INTEGRATED CIRCUIT** μ**PC1342V** T-74-05-01 50 to 110 W POWER AMPLIFIER DRIVER DESCRIPTION µPC1342V is a integrated monolithic circuit designed for 50 W to 110 W class HiFi audio power amplifier and consists of a input differential amplifier, a predriver circuit, a driver circuit and a over current protection circuit. FEATURES Low Distortion. 0.002 % TYP. (V_{CC} = ±46 V, f = 1 kHz, A_v = 30 dB, P_O = 80 W, R_L = 8 Ω with Power Transistor) 0.006 % TYP. (V_{CC} = ±46 V, f = 20 kHz, A_v = 30 dB, P_O = 80 W, R_L = 8 Ω with Power Transistor) • Wide Frequency Band. 900 kHz TYP. (-3 dB) Wide Power Band Width. 90 kHz TYP. (P_0 = 40 W, THD = 0.1 %) BLOCK DIAGRAM + V_{CC} D(Driver Stage) Muting +VCC P(Pre-amp Stage)NC NC -72 64 13



NOTE: The built-in over current circuit protects µPC1342V and cannot protect external power transistors.

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μ**PC1342V** 05E 23065 D

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ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

OLUTE MAXIMUM RATINGS (T _a = 2	5 °C)			T-74-05-01
Supply Voltage (Quiescent)	V _{CC1}	±75	v	
Supply Voltage (Operational)	V _{CC2}	±70	v	
Circuit Current	ICC (peak)	250	mA	
Allowable Package Dissipation	PD	7.5*	w	
Operational Temperature	Topt	-20 to +75	°C	
Storage Temperature	Tstg	-40 to +150	°C	
		* 100 x 100 x 2 mm	n Al heat sir	ık

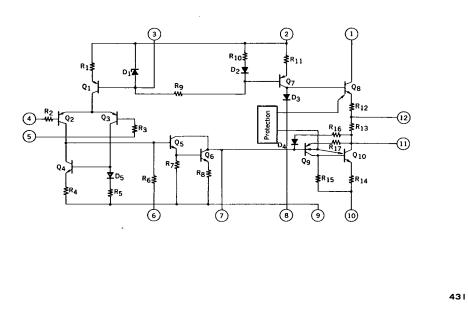
RECOMMENDED OPERATING CONDITIONS

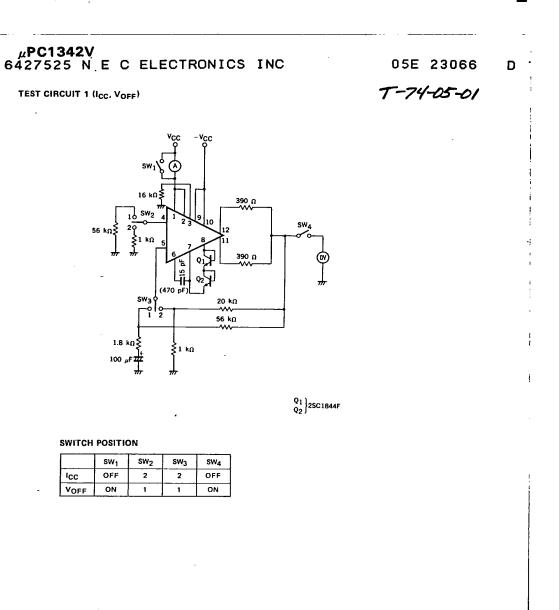
Supply Voltage (Operational)	V _{CC} = ±20 to ±52 V
Input Bias Resistance	R _{IN} = 1 to 50 to 100 kΩ
Power Transistor h _{FE}	h _{FE} ≧50 at P _O = 80 W, R _L = 8 Ω, T _i < 125 °C
Closed Loop Voltage Gain	A _v = 26 to 30 dB
Junction Temperature	T _j =20 to 125 °C

ELECTRICAL CHARACTERISTICS (V_{CC} = ±46 V, A_v = 30 dB, Use Standard Test Circuit, T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Output Offset Voltage	Voffset		±5	±50	mV	V _{IN} = 0
Quiescent Circuit Current	^I CC		20	40	mA	V _{IN} = 0
Maximum Output Voltage	VOM	25	28		v	THD=0.05%, f=20 Hz to 20 kHz
Open Loop Voltage Gain	Avo	80	95		dB	V _o = 1.5 V, f = 1 kHz
Output Noise Voltage	Vn		0.07	0.14	mV	R _G = 10 kΩ
Rolloff Frequency	fH		900		kHz	V _o = 1.5 V,3 dB
Supply Voltage Rejection Ratio	SVR	55	70		dB	R _G = 2.2 kΩ, f _{ripple} = 100 Hz, v _{ripple} = 1 V _{r.m.s.}

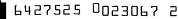
EQUIVALENT CIRCUIT

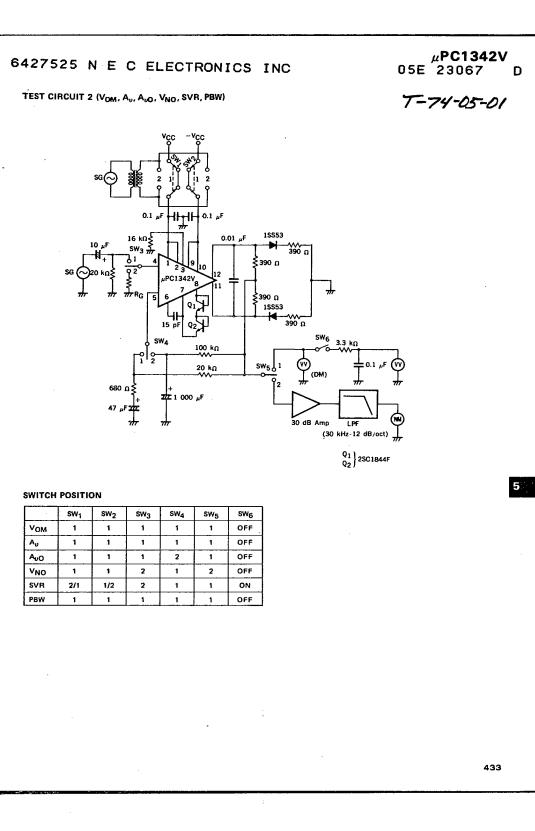




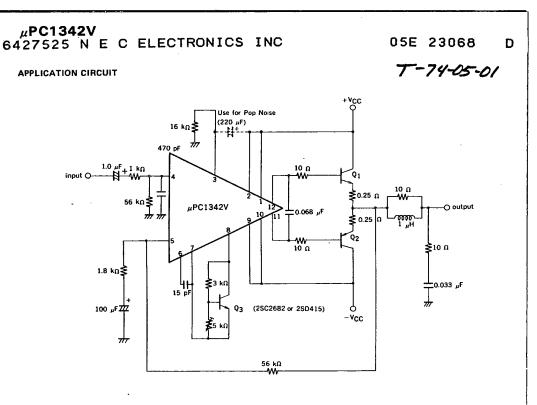
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RECOMMENDED POWER TRANSISTOR

Po	25 to 40 W	45 to 55 W	50 to 70 W	70 to 80 W	80 to 110 W
0 ₁	2SD1288 2SD2013	2SD1289 2SD1977	2SC3012 2SC4267	2SC2987 2SC2987A 2SC4268	2SC2987A 2SC4268 × 2
0 ₂	2SB965 2SB1336	2SB966 2SB1315	25A1232 25A1631	2SA1227 2SA1227A 2SA1632	2SA1227A 2SA1632 × 2

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